

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









RGPZ10BM40FH

430V 20A Ignition IGBT

BV _{CES}	430±30V			
I _C	20A			
V _{CE(sat) (Typ.)}	1.6V			
E _{AS}	250mJ			

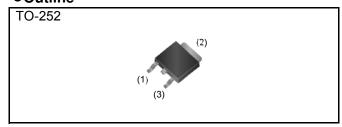
Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Self-Clamped Inductive Switching Energy
- 3) Built in Gate-Emitter Protection Diode
- 4) Qualified to AEC-Q101
- 5) Pb free Lead Plating; RoHS Compliant

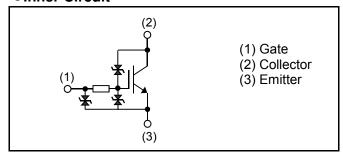
Applications

Ignition Coil Driver Circuits
Solenoid Driver Circuits

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Taping
	Reel Size (mm)	330
Typo	Tape Width (mm)	16
Туре	Basic Ordering Unit (pcs)	2,500
	Packing Code	TL
	Marking	RGPZ10BM40

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector - Emitter Voltage	V _{CES}	460	V	
Emitter-Collector Voltage (V _{GE} = 0\	V _{EC}	25	V	
Gate - Emitter Voltage	V_{GE}	±10	V	
Collector Current	I _C	20	А	
Avalanche Energy (Single Pulse)	T _j = 25°C	E _{AS}	250	mJ
	T _j = 150°C	E _{AS} *2	150	mJ
Power Dissipation		P _D	107	W
Operating Junction Temperature	T _j	-40 to +175	°C	
Storage Temperature	T _{stg}	−55 to +175	°C	

●Thermal Resistance

Parameter	Symbol	Values			Unit
- Alametei		Min.	Тур.	Max.	Offic
Thermal Resistance Junction - Case	$R_{\theta(j-c)}$	1	-	1.40	°C/W

●Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Davanatas	Symbol	Conditions	Values			1.1:4
Parameter		Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage		$I_C = 2mA$, $V_{GE} = 0V$				
	BV_CES	T _j = 25°C	400	430	460	V
		$T_j = -40 \text{ to } 175^{\circ}\text{C}^{*2}$	395	-	465	V
Emitter - Collector Breakdown Voltage	BV _{EC}	$I_{C} = -10 \text{mA}, V_{GE} = 0 \text{V}$	25	35	-	٧
Gate - Emitter Breakdown Voltage	BV _{GES}	$I_G = \pm 5$ mA, $V_{CE} = 0$ V	±12	-	±17	V
	I _{CES}	V _{CE} = 300V, V _{GE} = 0V				
Collector Cut - off Current		T _j = 25°C	-	-	7	μA
		$T_j = 150^{\circ}C^{*2}$	-	-	100	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 10V, V_{CE} = 0V$	-	-	±15	μΑ
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 10mA$				
		T _j = 25°C	1.3	1.7	2.1	V
		T _j = 150°C	-	1.3	-	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_{\rm C}$ = 10A, $V_{\rm GE}$ = 5V				
		T _j = 25°C	-	1.60	2.00	V
		T _j = 150°C	-	1.80	-	V

ullet Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Darameter	Cymphal	Conditions	Values			Lleit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 4A, V_{GE} = 4.5V$ $T_j = 25^{\circ}C$	-	1.17	1.50	V
	02(00.)	T _j = 150°C	-	1.13	-	V
		I _C = 10A, V _{GE} = 4V				
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	T _j = 25°C	-	1.70	2.10	V
		T _j = 150°C	-	1.90	-	V
Input Capacitance	C_{ies}	V _{CE} = 10V	-	1000	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	ı	175	ı	pF
Reverse Transfer Capacitance	C_{res}	f = 1MHz	ı	55	ı	
Total Gate Charge	Q_g	$V_{CE} = 15V, I_{C} = 10A,$ $V_{GE} = 5V$	-	14	-	nC
Turn - on Delay Time*1,*2	t _{d(on)}		0.09	0.17	0.50	
Rise Time*1,*2	t _r	$I_C = 8A, V_{CC} = 300V,$	0.10	0.18	0.50	μs
Turn - off Delay Time*1,*2	$t_{d(off)}$	$V_{GE} = 5V, R_G = 100\Omega,$ L=5mH, T _i =25°C	0.8	1.3	4.0	
Fall Time*1,*2	t _f	·	1.4	2.4	6.0	
Turn - on Delay Time ^{*1}	$t_{d(on)}$		1	0.16	ı	
Rise Time ^{*1}	t _r	$I_C = 8A, V_{CC} = 300V,$ $V_{GE} = 5V, R_G = 100\Omega,$	1	0.23	1	μs
Turn - off Delay Time*1	$t_{d(off)}$	L=5mH, T_j =150°C	1	1.5	ı	
Fall Time ^{*1}	t _f		ı	3.9	ı	
Accelerate Francis (Oingle Dules)	L	L = 5mH, V_{GE} = 5V, V_{CC} = 30V, R_{G} = 1k Ω ,				
Avalanche Energy (Single Pulse)	E_{AS}	T _j = 25°C	250	-	-	mJ
		$T_j = 150^{\circ}C^{*2}$	150	-	-	mJ
Gate Series Resistance	R_G		70	100	130	Ω

^{*1)} Assurance items according to our measurement definition (Fig.16)

^{*2)} Design assurance items

Electrical Characteristic Curves

Fig.1 Typical Output Characteristics

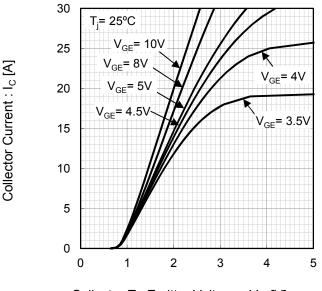
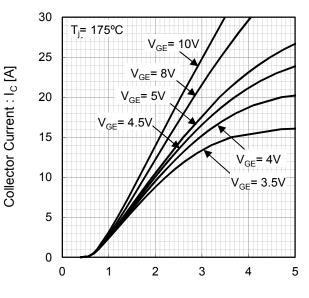


Fig.2 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Collector To Emitter Voltage : V_{CE}[V]

Fig.3 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

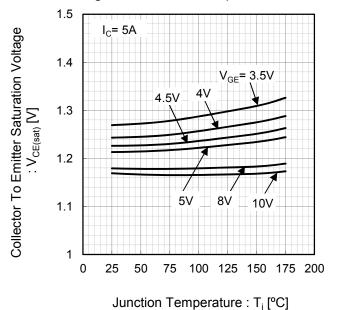
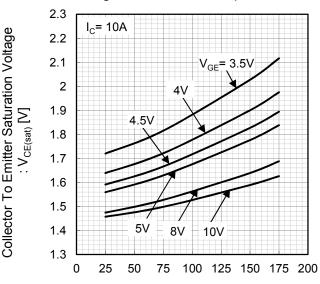


Fig.4 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

•Electrical Characteristic Curves

Fig.5 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

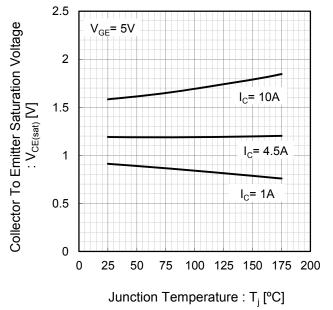
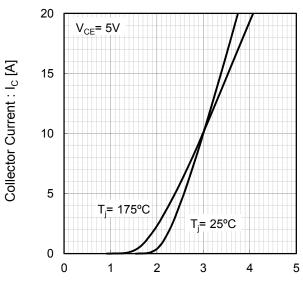
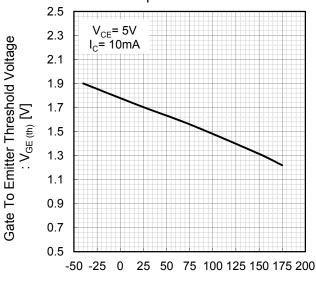


Fig.6 Typical Transfer Characteristics



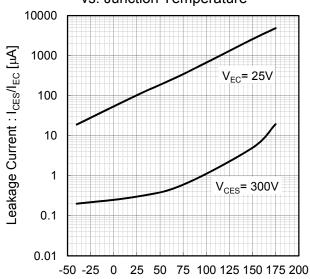
Gate To Emitter Voltage : V_{GE} [V]

Fig.7 Typical Gate To Emitter Threshold Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.8 Typical Leakage Current vs. Junction Temperature



Junction Temperature : T_i [°C]

Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Breakdown Voltage vs. Junction Temperature

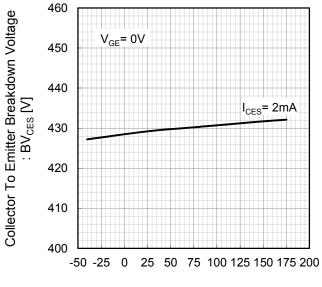
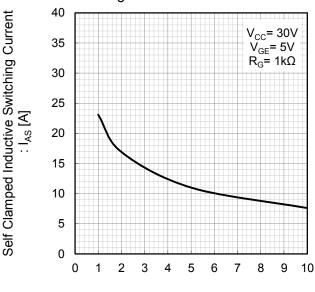


Fig.10 Typical Self Clamped Inductive Switching Current vs. Inductance



Junction Temperature : T_i [°C]

Inductance : L [mH]

Fig.11 Typical Gate Charge

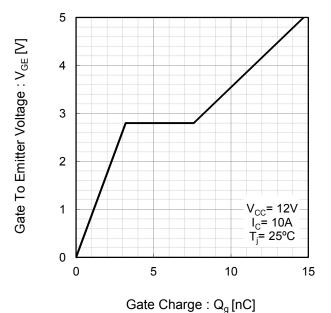
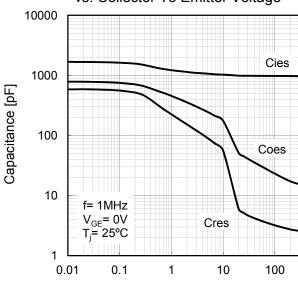


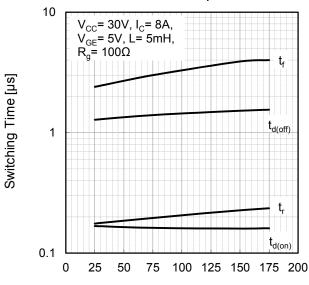
Fig.12 Typical Capacitance vs. Collector To Emitter Voltage



Collector To Emitter Voltage : V_{CE}[V]

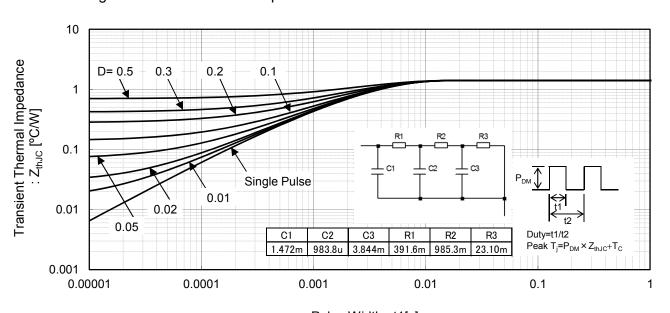
•Electrical Characteristic Curves

Fig.13 Typical Switching Time vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.14 Transient Thermal Impedance



Pulse Width: t1[s]

•Inductive Load Switching Circuit and Waveform

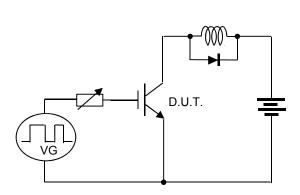


Fig.15 Inductive Load Switching Circuit

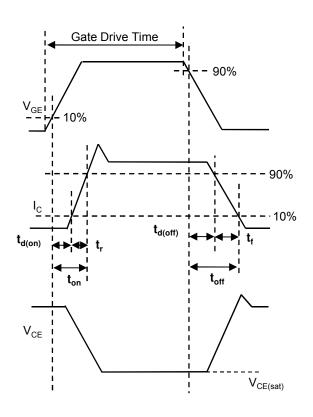
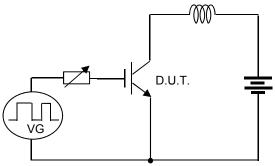


Fig.16 Inductive Load Switching Waveform

●Self Clamped Inductive Switching Circuit and Waveform



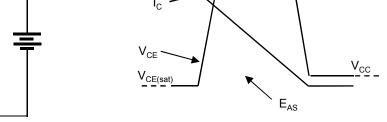


Fig.17 Self Clamped Inductive Switching Circuit Fig.18 Self Clamped Inductive Switching Waveform

 V_{clamp}

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